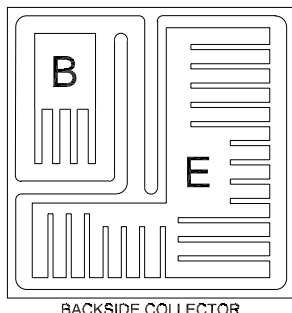


CP260-TIP122

NPN - Darlington Transistor Die

5.0 Amp, 100 Volt

The CP260-TIP122 die is a silicon NPN Darlington power transistor designed for low speed switching and amplifier applications.



MECHANICAL SPECIFICATIONS:

Die Size	70.87 x 70.87 MILS
Die Thickness	9.4 MILS
Base Bonding Pad Size	14.96 x 18.50 MILS
Emitter Bonding Pad Size	14.96 x 20.87 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ag - 12,000Å
Scribe Alley Width	3.15 mils
Wafer Diameter	4 INCHES
Gross Die Per Wafer	2,000

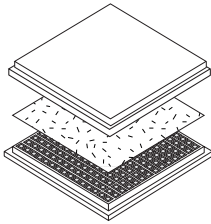
MAXIMUM RATINGS: ($T_C=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	5.0	A
Power Dissipation	P_D	65	W
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=100\text{V}$		0.2	mA
I_{CEO}	$V_{CE}=50\text{V}$		0.5	mA
I_{EBO}	$V_{EB}=5.0\text{V}$		2.0	mA
BV_{CEO}	$I_C=10\text{mA}$	100		V
BV_{CBO}	$I_C=100\mu\text{A}$	100		V
BV_{EBO}	$I_E=1\text{mA}$	5.0		V
$V_{CE(SAT)}$	$I_C=3.0\text{A}, I_B=12\text{mA}$		2.0	V
$V_{CE(SAT)}$	$I_C=5.0\text{A}, I_B=20\text{mA}$		4.0	V
$V_{BE(ON)}$	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}$		2.5	V
h_{FE}	$V_{CE}=3.0\text{V}, I_C=500\text{mA}$	1000		
h_{FE}	$V_{CE}=3.0\text{V}, I_C=3.0\text{A}$	1000		

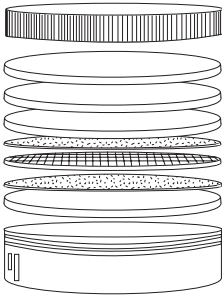
BARE DIE PACKING OPTIONS



BARE DIE IN TRAY (WAFFLE) PACK

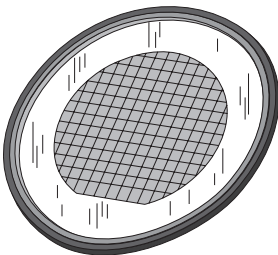
CT: Singulated die in tray (waffle) pack.
(example: CP211-PART NUMBER-CT)

CM: Singulated die in tray (waffle) pack 100% visually inspected as per MIL-STD-750, (method 2072 transistors, method 2073 diodes).
(example: CP211-PART NUMBER-CM)



UNSAWN WAFER

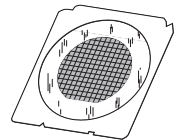
WN: Full wafer, unsawn, 100% tested with reject die inked.
(example: CP211-PART NUMBER-WN)



SAWN WAFER ON PLASTIC RING

WR: Full wafer, sawn and mounted on plastic ring,
100% tested with reject die inked.
(example: CP211-PART NUMBER-WR)

Please note: Sawn Wafer on Metal Frame (WS) is possible as a special order. Please contact your Central Sales Representative at 631-435-1110.



Visit the Central website for a complete listing of specifications:
www.centrasemi.com/bdspecs

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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